

**AMENDMENT TO THE SPECIFICATION**

***Please amend paragraph [0001] beginning page 1 as follows:***

[0001] The present invention ~~provides~~ relates to diamond, and more particularly a high-quality, large-size single crystal diamond that is suited to use in semiconductor device substrates and optical components, and ~~[[to]]~~ a method for manufacturing this diamond.

***Please amend paragraph [0002] beginning page 1 through page 3 as follows:***

[0002] Besides its high hardness and thermal conductivity, diamond also has many other excellent properties, such as a high optical transmittance and a wide bandgap, and is therefore widely used as a material for various tools, optical components, semiconductors, and electronic components, and its importance is only expected to grow in the future. In the past, naturally produced diamond has been used in industrial applications, but since natural diamond has a ~~quiet-variable~~ quite-variable quality, more and more manmade diamond is being used in an industrial setting. Diamond single crystals today are synthesized industrially under high temperature and pressure (several thousand degrees centigrade, and several tens of thousands of atmospheres). Super-high-pressure vessels that can withstand such high temperatures and pressures are extremely expensive, and there is a limit to their size, which imposes a limit to how large a single crystal can be synthesized by high-temperature, high-pressure methods. Ib-type diamond which contains nitrogen (N) as an impurity and is yellow in color has been synthesized by high-temperature, high-pressure methods and marketed in a diameter of about 1 cm, but this approximate size is thought to be the limit. Ila-type diamond which contains few impurities and is colorless and transparent can be mass-produced industrially in a size of only about a few millimeters.